Amendments to the Claims

1. (*Currently Amended*) A semiconductor device including a semiconductor body ~~(10)~~ comprising a source region ~~(13)~~ and a drain region ~~(14, 14a)~~ of a first conductivity type, having therebetween a channel-accommodating region ~~(15)~~, the drain region comprising a drain drift region (14) and a drain contact region ~~(14a)~~, with the drain drift region between the channel-accommodating region and the drain contact region, and the drain drift region being doped to a lesser degree than the drain contact region, an insulated gate ~~(11)~~ separated from the channel-accommodating region ~~(15)~~ by a gate insulating layer ~~(17)~~, and a localized region ~~(30,36,50)~~ in the drain drift region ~~(14a)~~ juxtaposed with the channel-accommodating region ~~(15)~~, the localized region ~~(30,36,50)~~ comprising alternating stripes ~~(31,32)~~ of the first conductivity type and a second, opposite conductivity type, which stripes extend laterally alongside the channel accommodating region ~~(15)~~ and away from the gate ~~(11)~~, the dimensions and doping levels of the stripes being such that the localized region provides a voltage-sustaining space-charge zone when depleted.

2. (*Currently Amended*) A device of claim 1, wherein the localised region ~~(30, 36, 50)~~ adjoins the channel-accommodating region.

3. (*Currently Amended*) A device of claim 1, wherein the localised region ~~(36)~~ is laterally spaced from the gate insulating layer.

4. (*Currently Amended*) ~~A device of claim 1, 2~~ A device of claim 1, wherein the average doping level of the localized region ~~(30,36,50)~~ is substantially the same as that of an adjacent portion of the drain drift region.

5. (*Currently Amended*) ~~A device of claim 1, 2, or 3,~~ A device of claim 1, wherein the gate ~~(11)~~ is provided in a trench ~~(20)~~, the trench extending through the channel-accommodating region ~~(15)~~ into the drain drift region ~~(14a)~~.

6. (*Currently Amended*) A device of Claim 5 comprising a plurality of adjacent cells, each including a gate ~~(11)~~ in a trench ~~(20)~~, wherein a deep diffusion region ~~(40)~~ of the

second conductivity type is provided between adjacent trenches, the deep diffusion region ~~(40)~~ being doped co a greater extent that the channel accommodating region ~~(15)~~ .

7. (*Currently Amended*) A device of Claim 5 wherein the lower boundary ~~(30b)~~ of the localized region ~~(30,36)~~ is above the bottom of the gate trenches.

8. (*Currently Amended*) A device of claim 1, 2 or 3 wherein the channel-accommodating region ~~(15)~~ is a region of an opposite, second conductivity type.

9. (*Currently Amended*) A method of manufacturing a semiconductor device including a semiconductor body ~~(10)~~ comprising a source region ~~(13)~~ and a drain region ~~(14,14a)~~ of a first conductivity type, having therebetween a channel-accommodating region ~~(15)~~, the drain region comprising a drain drift region ~~(14a)~~ and a drain contact region ~~(14)~~, with the drain drift region between the channel-accommodating region and the drain contact region, and the drain drift region being doped to a lesser degree that the drain contact region, and an insulated gate ~~(11)~~ separated from the channel-accommodating region ~~(15)~~ by a gate insulating layer ~~(17)~~, the method including the step of:

forming a localised region ~~(30,36,50)~~ in the drain drift region ~~(14a)~~ juxtaposed with the channel-accommodating region ~~(15)~~, the localized region ~~(30,36,50)~~ comprising alternating stripes ~~(31, 32)~~ of the first conductivity type and a second, opposite conductivity type, which.stripes extend laterally alongside the channel-accommodating region ~~(15)~~ and away from the gate ~~(11)~~.

10. (*Currently Amended*) A method of Claim 9 wherein the localised region ~~(30,36,50)~~ forming step comprises implanting a dopant of one of the first and second conductivity types, defining a striped mask ~~(35)~~ over the semiconductor body ~~(10)~~, and implanting a dopant of the other of the first and second conductivity types.